

SURFACE MOUNT SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V CURRENT: 1.0 A

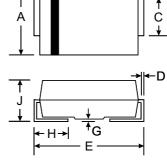
Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: SMB(DO-214AA),Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.093 grams (approx.)





- B ·

SMB(DO-214AA)							
Dim	Min	Max					
Α	3.30	3.94					
В	4.06	4.70					
с	1.91	2.21					
D	0.15	0.31					
E	5.00	5.59					
G	0.10	0.20					
н	0.76	1.52					
J	2.00	2.62					
All Dimensions in mm							

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic		Symbol	S1AB	S1BB	S1DB	S1GB	S1JB	S1KB	S1MB	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage		VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current	@T _L = 100°C	lo	1.0						А	
Non-Repetitive Peak Forward Surge 8.3ms Single half sine-wave superir rated load (JEDEC Method)		IFSM				30				А
Forward Voltage	@I _F = 1.0A	Vfm	1.10							V
	@T _A = 25°C @T _A = 125°C	IRM	5.0 200					μA		
Reverse Recovery Time (Note 1)		trr				2.5				μS
Typical Junction Capacitance (Note	2)	Cj				15				pF
Typical Thermal Resistance (Note 3	3)	R∉JL				30				K/W
Operating and Storage Temperature Range		Тј, Тѕтс	-65 to +175							°C

Note: 1. Measured with I_{F} = 0.5A, I_{R} = 1.0A, I_{rr} = 0.25A,

2. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.

3. Mounted on P.C. Board with 8.0mm² land area.



